

## E Series Power MOSFET with Fast Body Diode



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

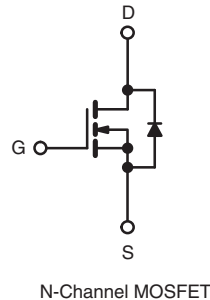
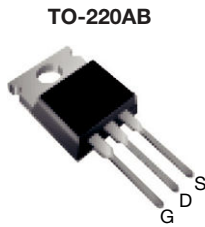
PRODUCT SUMMARY	
$V_{DS}$ (V) at $T_J$ max.	700
$R_{DS(on)}$ max. at 25 °C ( $\Omega$ )	$V_{GS} = 10$ V   0.18
$Q_g$ max. (nC)	106
$Q_{gs}$ (nC)	14
$Q_{gd}$ (nC)	33
Configuration	Single

### FEATURES

- Fast Body Diode MOSFET using E Series Technology
- Reduced  $t_{rr}$ ,  $Q_{rr}$ , and  $I_{RRM}$
- Low Figure-of-Merit (FOM)  $R_{on} \times Q_g$
- Low Input Capacitance ( $C_{iss}$ )
- Low Switching Losses Due to Reduced  $Q_{rr}$
- Ultra Low Gate Charge ( $Q_g$ )
- Avalanche Energy Rated (UIS)
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

### APPLICATIONS

- Telecommunications
  - Server and Telecom Power Supplies
- Lighting
  - High-Intensity Discharge (HID)
  - Fluorescent Ballast Lighting
- Consumer and Computing
  - ATX Power Supplies
- Industrial
  - Welding
  - Battery Chargers
- Renewable Energy
  - Solar (PV Inverters)
- Switch Mode Power Supplies (SMPS)
  - LCC
  - Phase shifted Bridge (ZVS)
  - 3-Level Inverter
  - AC/DC Bridge



ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free and Halogen-free	SiHP21N65EF-GE3


ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	650	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Gate-Source Voltage AC ( $f > 1$ Hz)		30	
Continuous Drain Current ( $T_J = 150$ °C)	$V_{GS}$ at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	55	
Linear Derating Factor		1.7	W/°C
Single Pulse Avalanche Energy <sup>b</sup>	$E_{AS}$	367	mJ
Maximum Power Dissipation	$P_D$	208	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 150	°C
Drain-Source Voltage Slope	$dV/dt$	$T_J = 125$ °C	V/ns
Reverse Diode $dV/dt^d$		31	
Soldering Recommendations (Peak Temperature) <sup>c</sup>	for 10 s	300	°C

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 5.1$  A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$ ,  $dI/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C.



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.5	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		650	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$		-	0.67	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2	-	4	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	$\mu\text{A}$
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 11\text{ A}$	-	0.15	0.18	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 30\text{ V}, I_D = 11\text{ A}$		-	7.0	-	S
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$		-	2322	-	$\mu\text{F}$
Output Capacitance	$C_{oss}$			-	105	-	
Reverse Transfer Capacitance	$C_{rss}$			-	4	-	
Effective Output Capacitance, Energy Related <sup>a</sup>	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 520\text{ V}, V_{GS} = 0\text{ V}$		-	84	-	$\mu\text{F}$
Effective Output Capacitance, Time Related <sup>b</sup>	$C_{o(tr)}$			-	293	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 11\text{ A}, V_{DS} = 520\text{ V}$	-	71	106	nC
Gate-Source Charge	$Q_{gs}$			-	14	-	
Gate-Drain Charge	$Q_{gd}$			-	33	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 520\text{ V}, I_D = 11\text{ A}, V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$		-	22	44	ns
Rise Time	$t_r$			-	34	68	
Turn-Off Delay Time	$t_{d(off)}$			-	68	102	
Fall Time	$t_f$			-	42	84	
Gate Input Resistance	$R_g$	$f = 1\text{ MHz}, \text{open drain}$		-	0.78	-	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	21	A
Pulsed Diode Forward Current	$I_{SM}$			-	-	55	
Diode Forward Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 11\text{ A}, V_{GS} = 0\text{ V}$		-	0.9	1.2	V
Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 11\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, V_R = 25\text{ V}$		-	160	-	ns
Reverse Recovery Charge	$Q_{rr}$			-	1.2	-	$\mu\text{C}$
Reverse Recovery Current	$I_{RRM}$			-	14	-	A

**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .
- b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

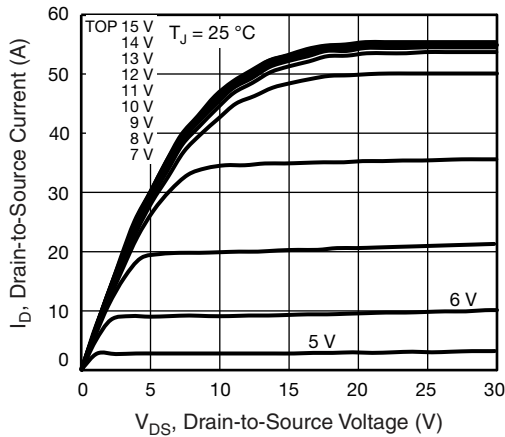


Fig. 1 - Typical Output Characteristics

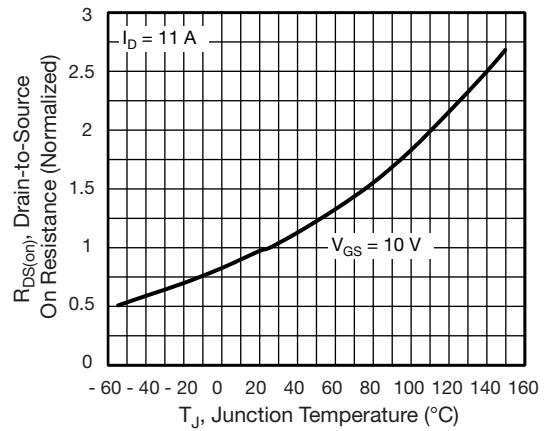


Fig. 4 - Normalized On-Resistance vs. Temperature

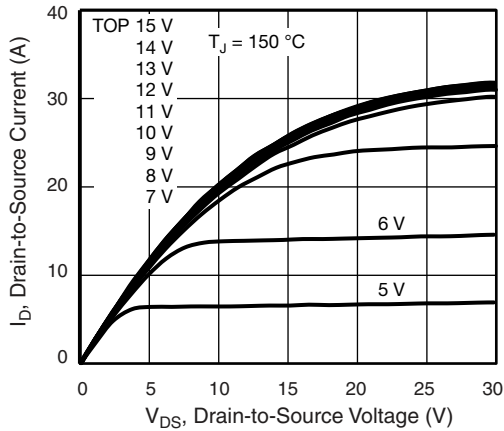


Fig. 2 - Typical Output Characteristics

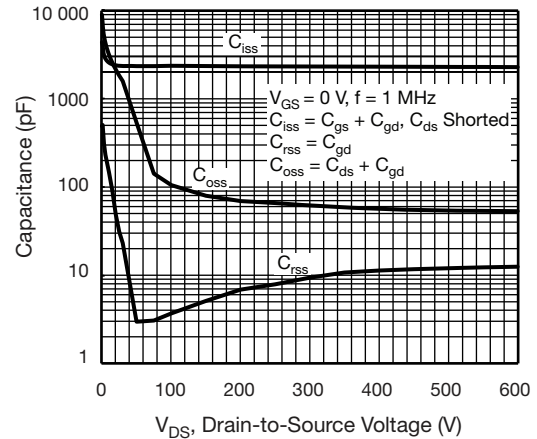


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

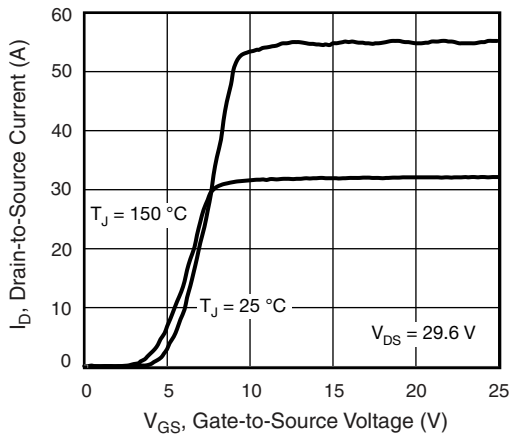


Fig. 3 - Typical Transfer Characteristics

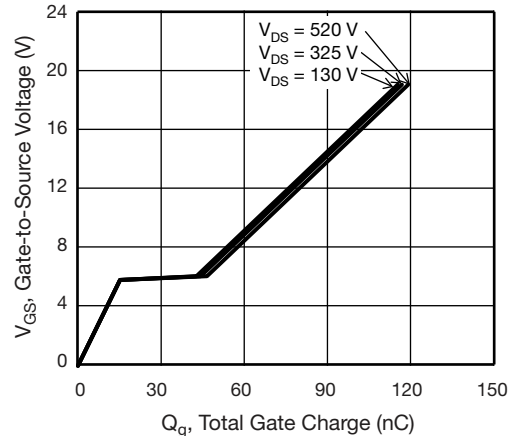


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

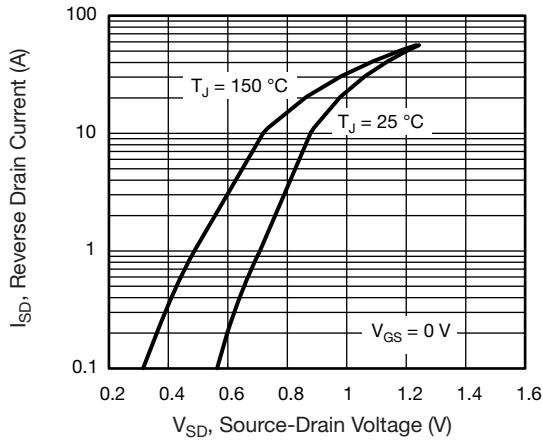


Fig. 7 - Typical Source-Drain Diode Forward Voltage

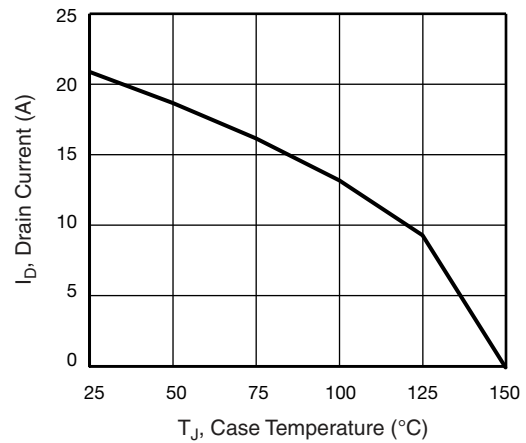


Fig. 9 - Maximum Drain Current vs. Case Temperature

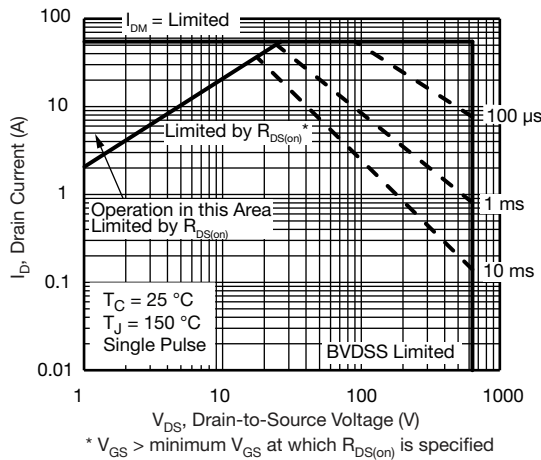


Fig. 8 - Maximum Safe Operating Area

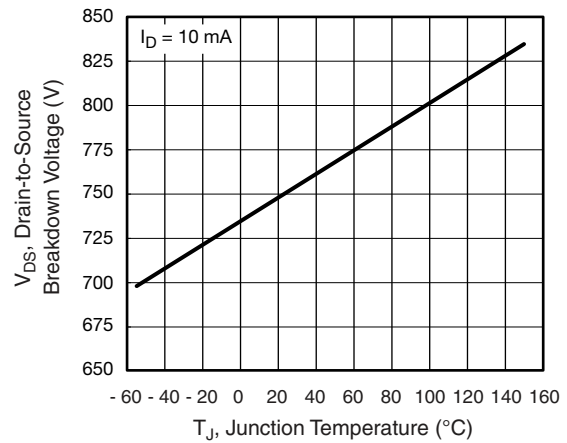


Fig. 10 - Temperature vs. Drain-to-Source Voltage

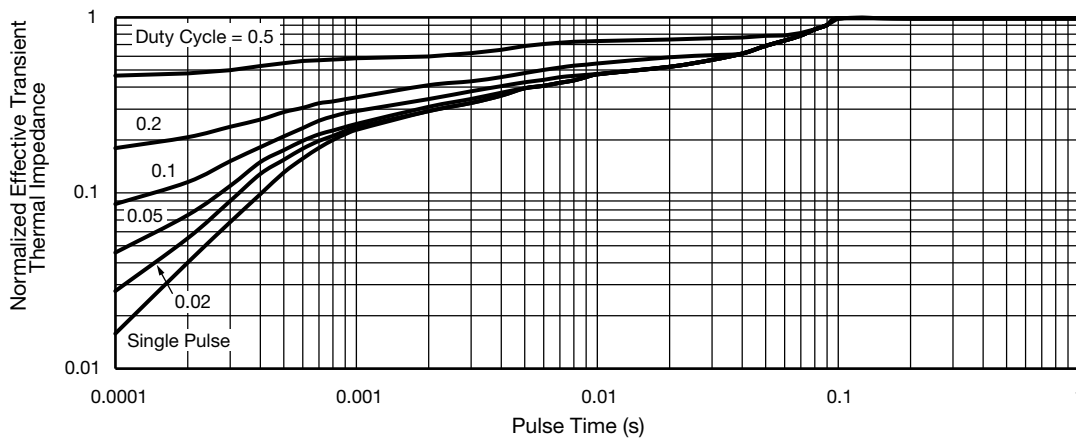


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case

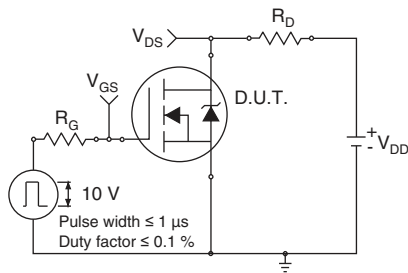


Fig. 12 - Switching Time Test Circuit

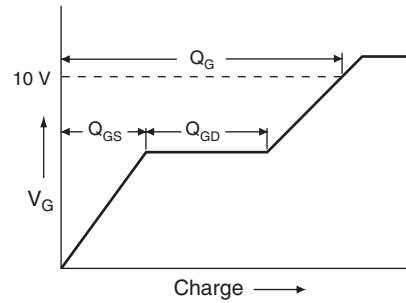


Fig. 16 - Basic Gate Charge Waveform

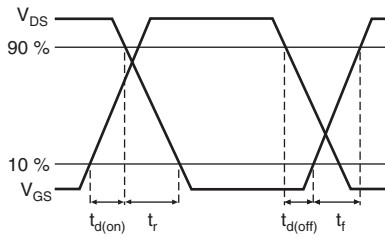


Fig. 13 - Switching Time Waveforms

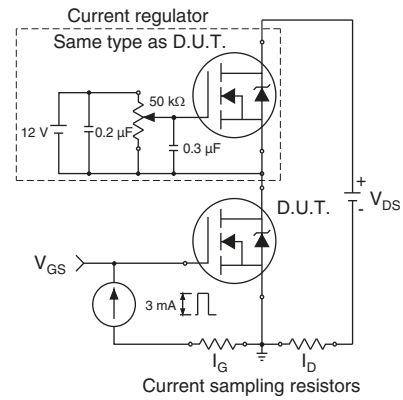


Fig. 17 - Gate Charge Test Circuit

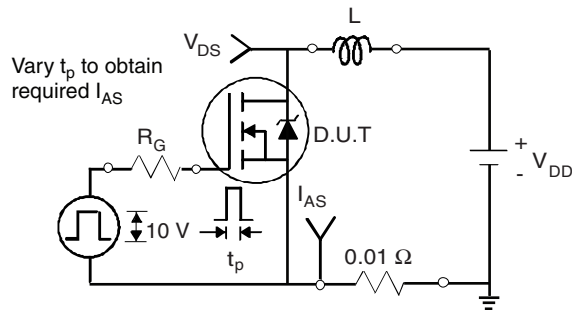


Fig. 14 - Unclamped Inductive Test Circuit

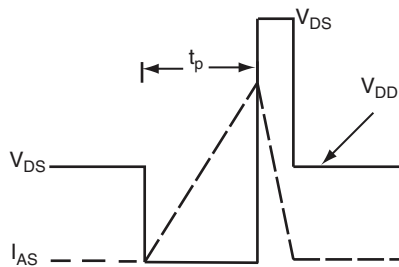
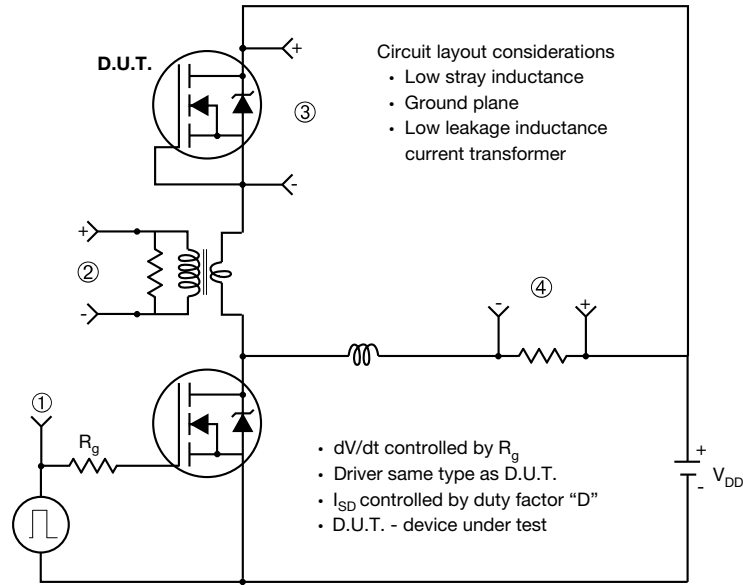


Fig. 15 - Unclamped Inductive Waveforms

Peak Diode Recovery  $dV/dt$  Test Circuit



Note

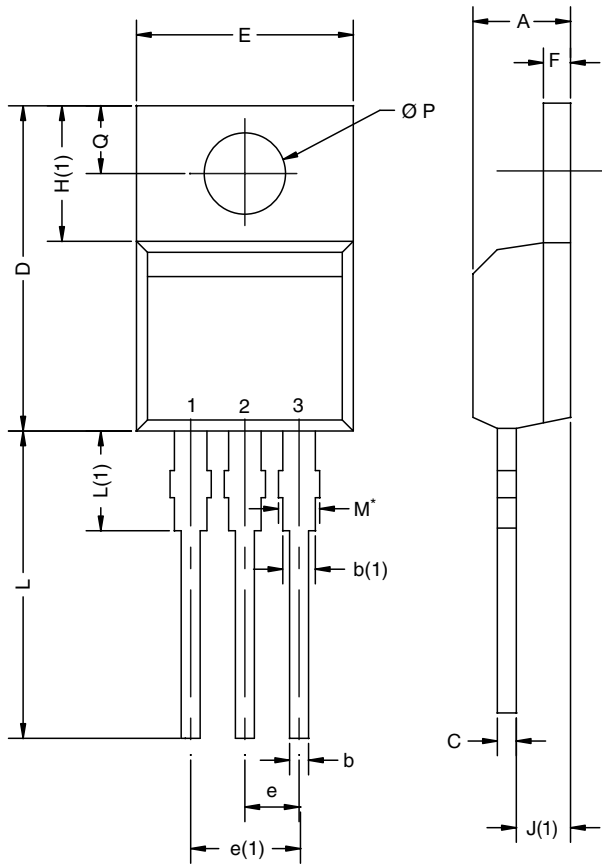
a.  $V_{GS} = 5\text{ V}$  for logic level devices

Fig. 18 - For N-Channel

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TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: T13-0724-Rev. O, 14-Oct-13  
DWG: 5471

Note

\* M = 1.32 mm to 1.62 mm (dimension including protrusion)  
Heatsink hole for HVM



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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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